

NVDSH50120C

Silicon Carbide Schottky Diode, 1200V, 50A, TO-247-2LD

Product Overview

For complete documentation, see the data sheet.

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability to silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size and cost.

Features

- Max Junction Temperature
- Avalanche Rated
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery / No Forward Recovery
- AEC-Q101 qualified and PPAP Capable

Benefits

- $T_j = 175\text{ }^\circ\text{C}$
- 380 mJ

Applications

- Automotive HEV-EV Onboard Chargers
- Automotive HEV-EV DC-DC Converters

End Products

- Automotive HEV-EV Onboard Chargers
- Automotive HEV-EV DC-DC Converters

Part Electrical Specifications

Product	Pricing (\$/Unit)	Compliance	Status	Family	Configuration	V_{RRM} (V)	$I_{F(ave)}$ (A)	V_F (Max)	I_{FSM} (A)	I_R (Max) (μA)	Package Type
NVDSH50120C	15.0812		Active	D3	Single	1200	50	1.75	231	200	TO-247-2LD